

For EMI Filtering and ESD Protection.

FEATURES

- EMI/RFI filtering.
- ESD Protection to IEC 61000-4-2 Level 4.
- Low insertion loss.
- Good attenuation of high frequency signals.
- Low clamping voltage.
- Low operating and leakage current.

APPLICATIONS

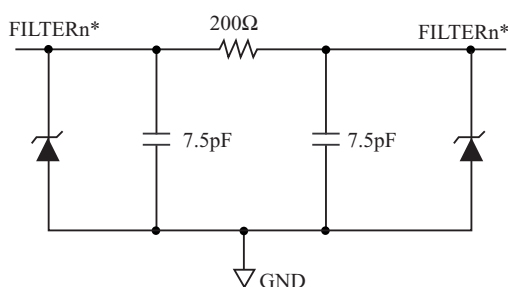
- Cell phone handsets.
- RF communications equipment.

MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
DC Power Per Resistor	P_R	100	mW
Power Dissipation	* P_D	400	
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 ~ 150	°C

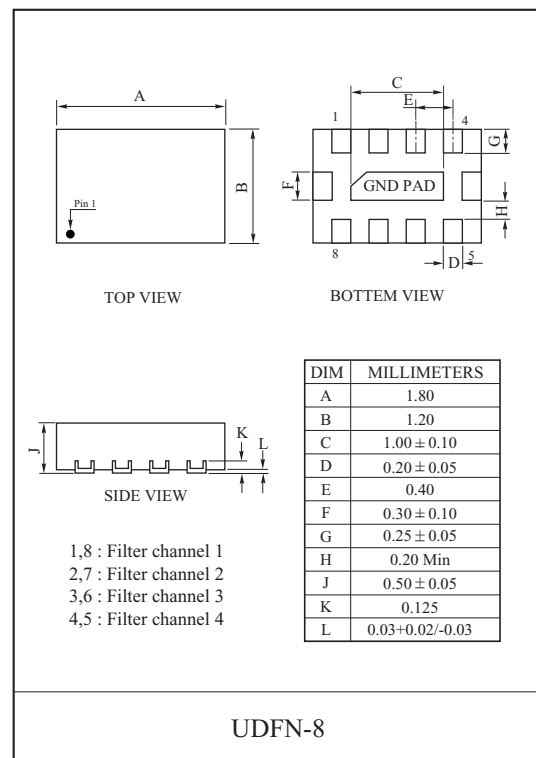
* Total Package Power Dissipation

EQUIVALENT CIRCUIT

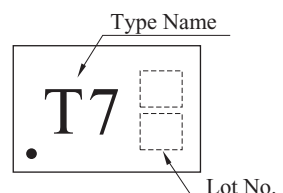


ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Stand-Off Voltage	V_{RWM}	-	-	-	5	V
Reverse Breakdown Voltage	V_{BR}	$I_t=1mA$	6	-	-	V
Reverse Leakage Current	I_R	$V_{RWM}=3V$	-	-	0.1	μA
Cutoff Frequency	f_{3dB}	$V_R=0V$, $Z_{SOURCE}=50\ \Omega$, $Z_{LOAD}=50\ \Omega$	-	210	-	MHz
Attenuation	$ S_{21} ^2$	$V_R=0V$, $f=800MHz\sim 3GHz$, $Z_{SOURCE}=50\ \Omega$, $Z_{LOAD}=50\ \Omega$	25	-	-	dB
Resistance	R	Between Input and Output	-	200	-	Ω
Capacitance	C	$V_R=2.5V$, Between I/O Pins and GND	-	15	-	pF

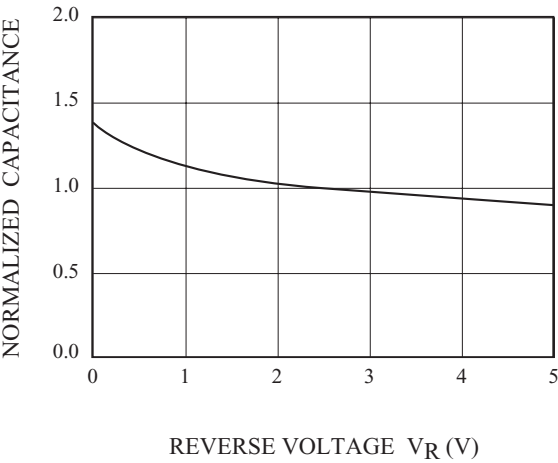


MARKING

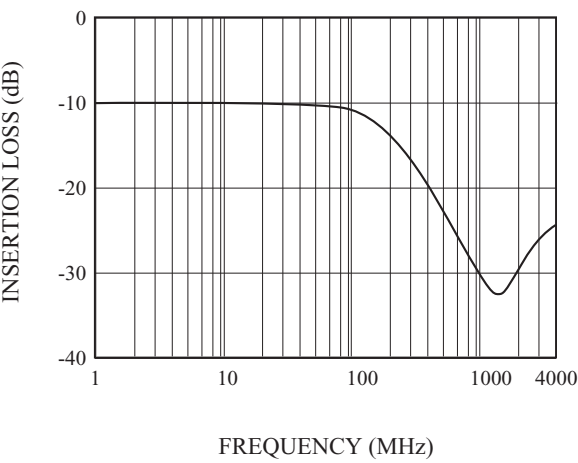


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$C_J - V_R$



$S_{21} - f$



$I_R - V_R$

